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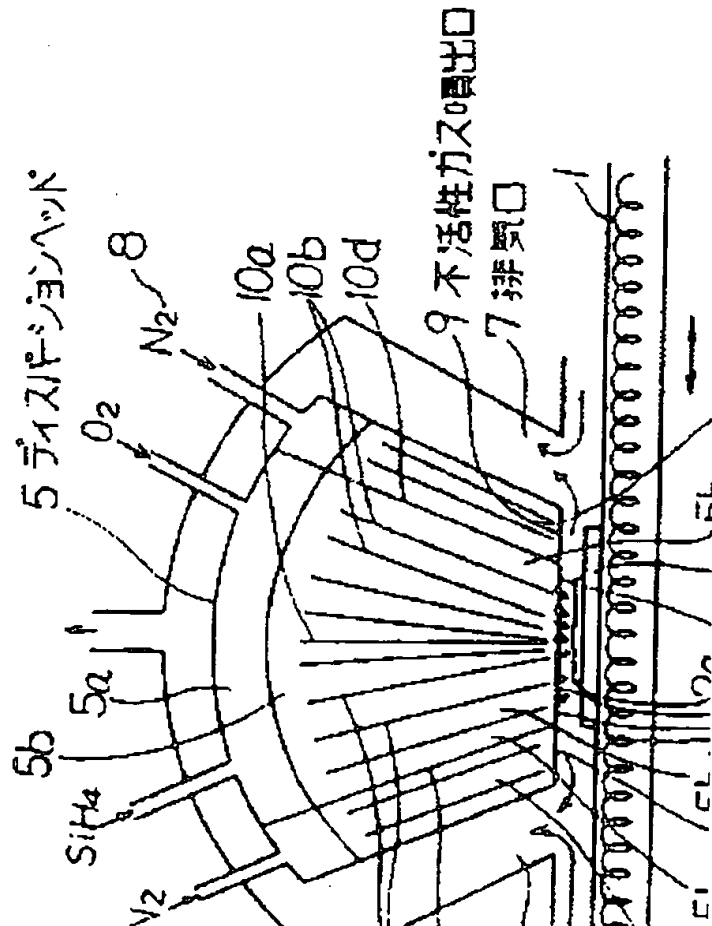
(74) Representative:

(54) ATMOSPHERIC  
PRESSURE CVD DEVICE

(57) Abstract:

**PURPOSE:** To blow a sufficient reaction gas to a step part and to improve step coverage by providing plural reaction gas blow ports of different blow directions to a dispersion head and providing an inert gas blow port and discharge port to the outside thereof.

**CONSTITUTION:** A mixing chamber 5a for mixing gaseous silane 3 and gaseous oxygen and a distributing chamber 5b for distributing a gaseous mixture to a susceptor 1 side are provided to the dispersion head 5 installed right above the susceptor 1. The distributing chamber 5b is divided to the plural distributing chambers 5b1W5bn by partition plates 10a, 10b of different angles of inclination and ejection ports 6W are provided toward the specific regions of a wafer mounting part on the extension line thereof to blow the reaction gas to



the step 2a of a semiconductor device 2 from a diagonal direction. An inert gas ejection port 9 is opened to enclose the outside circumference of the gas ejection ports 6W and the discharge port 7 is provided on the outside thereof to partition the reaction gas and the atm. air by the inert gas 8, by which the abnormal growth of the film and the adhesion of the rubber onto the semiconductor device 2 are prevented.

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